

Features

- Advanced Shield Gate Trench technology
- Super Low Gate Charge
- High-Speed Switching
- 100% EAS Guaranteed
- Green Device Available

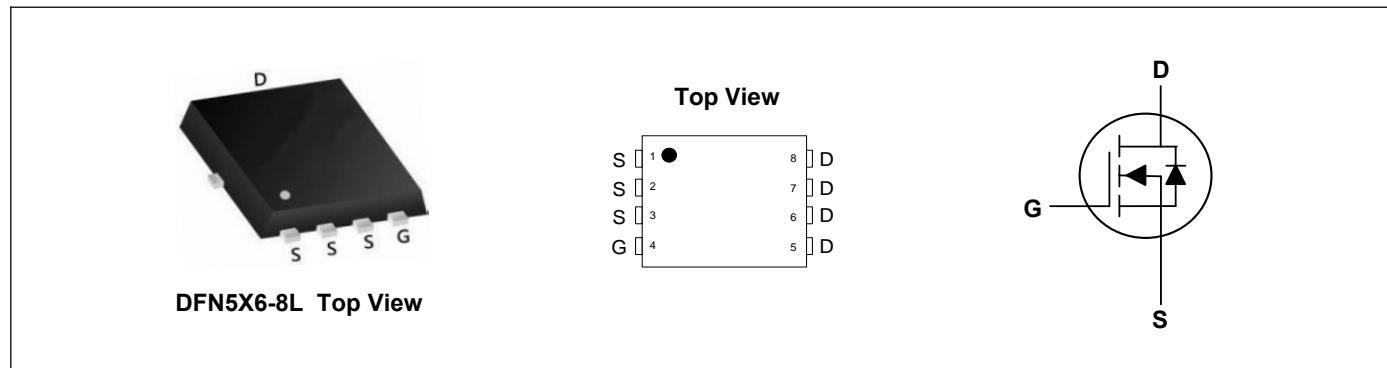
Product Summary



| | | |
|----------------------------------|------|----|
| V_{DS} | 30 | V |
| I_D | 200 | A |
| $R_{DS(ON)}$ (at $V_{GS}=10V$) | 0.85 | mΩ |
| $R_{DS(ON)}$ (at $V_{GS}=4.5V$) | 1.45 | mΩ |

Applications

- High Frequency Point-of-Load,Synchronous Buck Converter
- Networking DC-DC Power System
- Load Switch



Absolute Maximum Ratings($T_c=25^\circ\text{C}$, unless otherwise noted)

| Parameter | Symbol | Rating | Units |
|--|-----------|------------|-------|
| Drain-Source Voltage | V_{DS} | 30 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Continuous Drain Current ¹ | I_D | 200 | A |
| Pulsed Drain Current ² | I_{DM} | 644 | A |
| Single Pulse Avalanche Energy ³ | E_{AS} | 1058 | mJ |
| Total Power Dissipation | P_D | 35 | W |
| Storage Temperature Range | T_{STG} | -55 to 175 | °C |
| Operating Junction Temperature Range | T_J | -55 to 175 | °C |

Thermal Characteristics

| Parameter | Symbol | Typ | Max | Unit |
|--|-----------------|-----|------|------|
| Thermal Resistance Junction-Ambient ¹ | $R_{\theta JA}$ | --- | 62.5 | °C/W |
| Thermal Resistance Junction-Case ¹ | $R_{\theta JC}$ | --- | 3.5 | °C/W |

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|-----------------------------------|----------------------------|--|-----|------|-----------|------------------|
| Drain-Source Breakdown Voltage | BV_{DSS} | $V_{\text{GS}}=0\text{V}$, $I_D=250\mu\text{A}$ | 30 | --- | --- | V |
| Static Drain-Source On-Resistance | $R_{\text{DS}(\text{ON})}$ | $V_{\text{GS}}=10\text{V}$, $I_D=50\text{A}$ | --- | 0.75 | 0.85 | $\text{m}\Omega$ |
| | | $V_{\text{GS}}=4.5\text{V}$, $I_D=30\text{A}$ | --- | 1.25 | 1.45 | $\text{m}\Omega$ |
| Gate Threshold Voltage | $V_{\text{GS}(\text{th})}$ | $V_{\text{GS}}=V_{\text{DS}}$, $I_D=250\mu\text{A}$ | 1.0 | --- | 2.0 | V |
| Drain-Source Leakage Current | I_{DSS} | $V_{\text{DS}}=24\text{V}$, $V_{\text{GS}}=0\text{V}$ | --- | --- | 1 | μA |
| Gate-Source Leakage Current | I_{GSS} | $V_{\text{GS}}=\pm 20\text{V}$, $V_{\text{DS}}=0\text{V}$ | --- | --- | ± 100 | nA |
| Total Gate Charge | Q_g | $V_{\text{DS}}=15\text{V}$, $V_{\text{GS}}=10\text{V}$, $I_D=50\text{A}$ | --- | 190 | --- | nC |
| Gate-Source Charge | Q_{gs} | | --- | 40 | --- | |
| Gate-Drain Charge | Q_{gd} | | --- | 33 | --- | |
| Turn-On Delay Time | $T_{\text{d}(\text{on})}$ | $V_{\text{DS}}=15\text{V}$, $V_{\text{GS}}=10\text{V}$, $R_G=4.5\Omega$, $R_L=0.3\Omega$, $I_D=50\text{A}$ | --- | 25 | --- | ns |
| Rise Time | T_r | | --- | 94 | --- | |
| Turn-Off Delay Time | $T_{\text{d}(\text{off})}$ | | --- | 148 | --- | |
| Fall Time | T_f | | --- | 98 | --- | |
| Input Capacitance | C_{iss} | $V_{\text{DS}}=15\text{V}$, $V_{\text{GS}}=0\text{V}$, $f=1\text{MHz}$ | --- | 9950 | --- | pF |
| Output Capacitance | C_{oss} | | --- | 1260 | --- | |
| Reverse Transfer Capacitance | C_{rss} | | --- | 475 | --- | |

Drain-Source Diode Characteristics

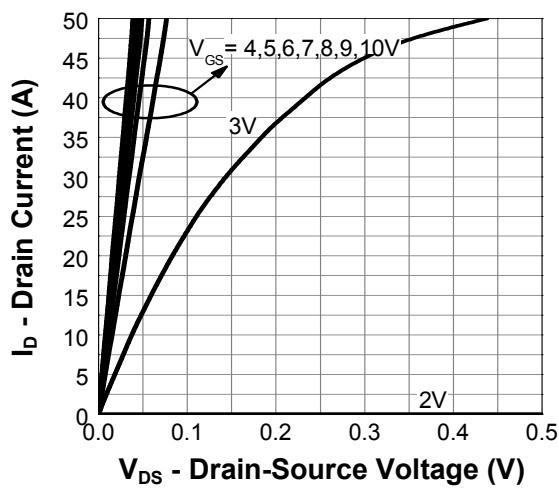
| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|--|-----------------|---|-----|-----|-----|------|
| Continuous Source Current ¹ | I_s | | --- | --- | 200 | A |
| Diode Forward Voltage ² | V_{SD} | $V_{\text{GS}}=0\text{V}$, $I_s=50\text{A}$, $T_J=25^\circ\text{C}$ | --- | --- | 1.3 | V |
| Reverse Recovery Time | t_{rr} | $I_f=40\text{A}$ | --- | 35 | --- | nS |
| | Q_{rr} | $dI/dt=100\text{A}/\mu\text{s}$, $T_J=25^\circ\text{C}$ | --- | 23 | --- | nC |

Note:

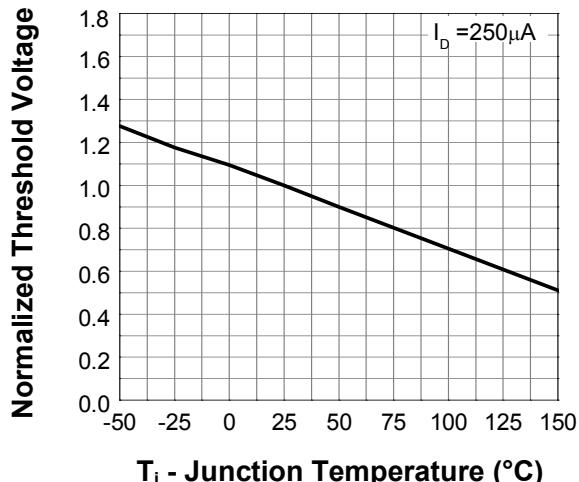
1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
2. The data tested by pulsed, pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
3. The EAS data shows Max. rating . The test condition is $V_{\text{DD}}=30\text{V}$, $L=1\text{mH}$

Typical Characteristics

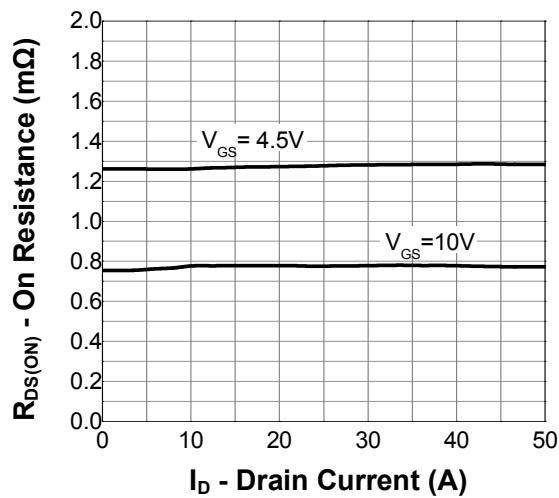
Output Characteristics



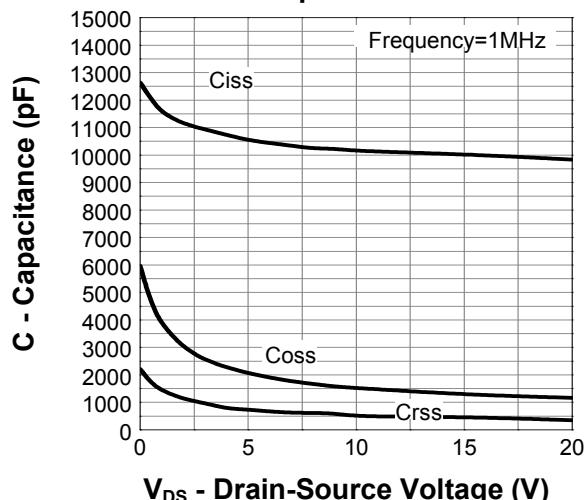
Normalized Threshold Voltage



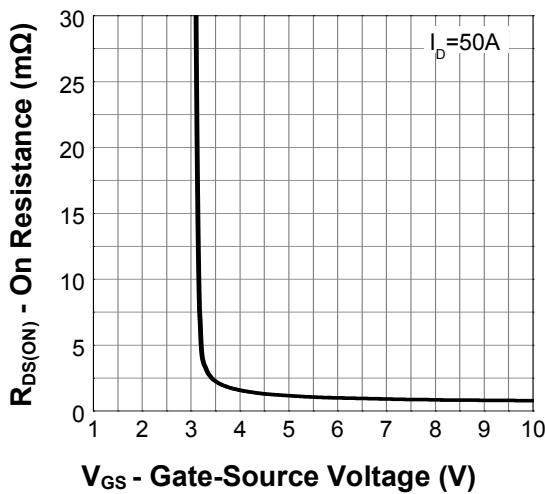
On Resistance



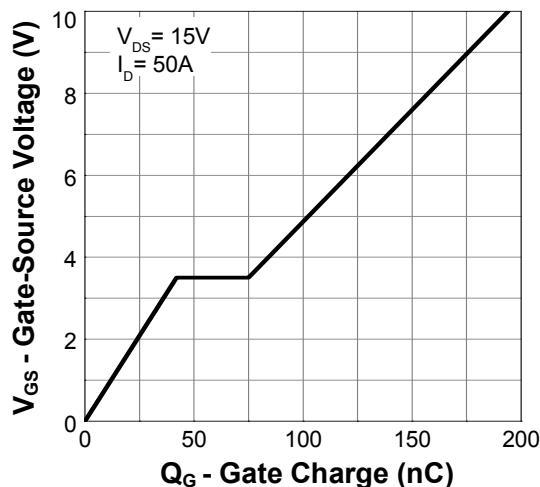
Capacitance

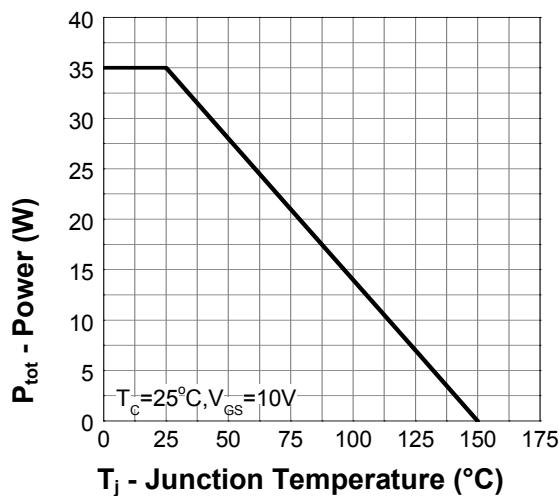
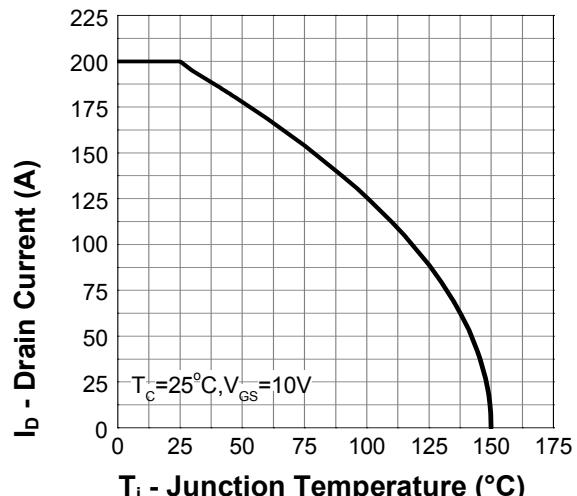
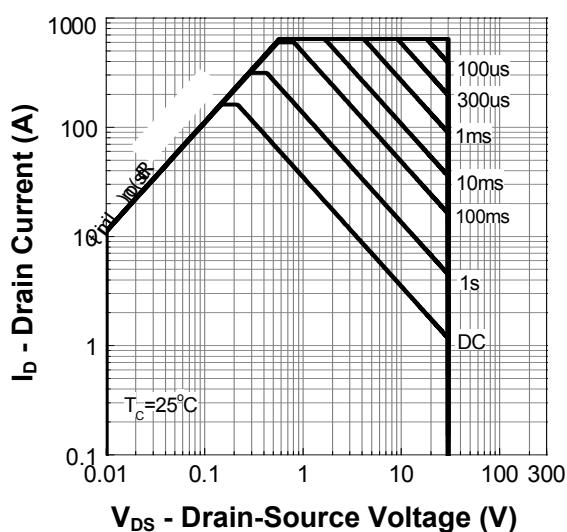
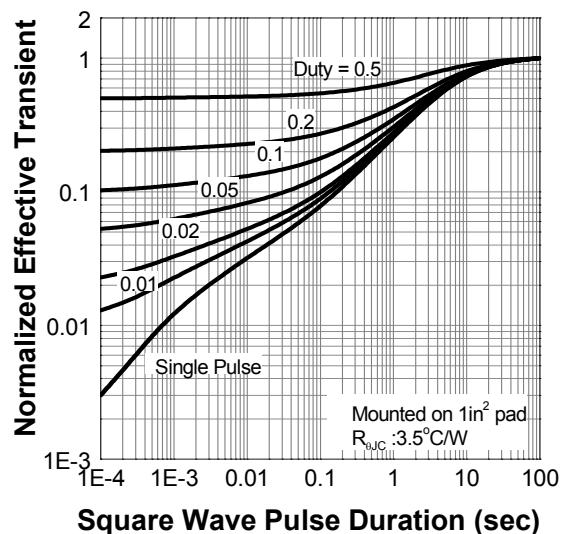


Transfer Characteristics

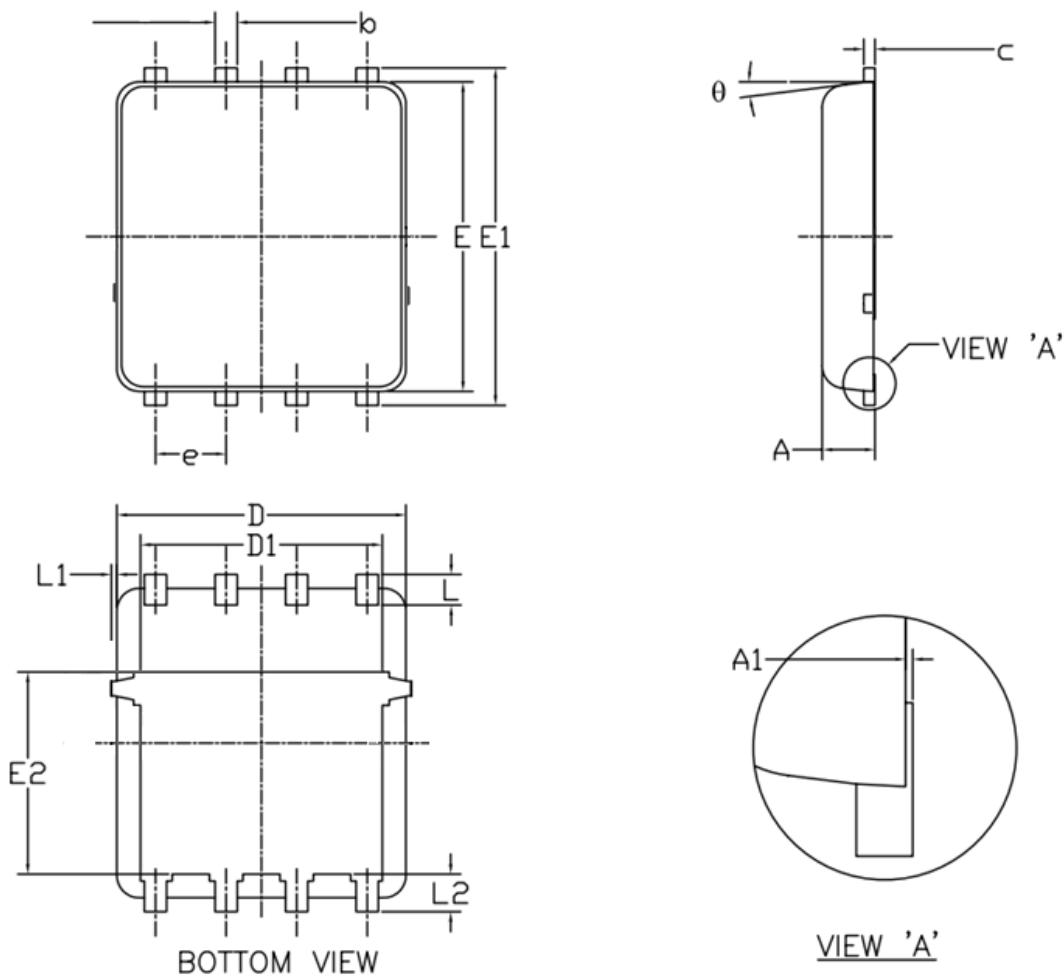


Gate Charge



Power Capability

Current Capability

Safe Operation Area

Transient Thermal Impedance


DFN5X6-8L Package Outline Dimensions



| Symbol | Dimensions (unit:mm) | | | Symbol | Dimensions (unit:mm) | | |
|---------------|-----------------------------|------------|------------|---------------|-----------------------------|------------|------------|
| | Min | Typ | Max | | Min | Typ | Max |
| A | 0.90 | 1.00 | 1.20 | E1 | 5.90 | 6.10 | 6.35 |
| A1 | 0.00 | -- | 0.05 | E2 | 3.38 | 3.58 | 3.92 |
| b | 0.30 | 0.40 | 0.51 | e | 1.27 BSC | | |
| c | 0.20 | 0.25 | 0.33 | L | 0.51 | 0.61 | 0.71 |
| D | 4.80 | 4.90 | 5.40 | L1 | -- | -- | 0.15 |
| D1 | 3.61 | 4.00 | 4.25 | L2 | 0.41 | 0.51 | 0.61 |
| E | 5.65 | 5.80 | 6.06 | θ | 0° | -- | 12° |